

ABSTRACT

As the critical dimensions of liftoff patterns grow smaller, it becomes increasingly more difficult to make liftoff resists that have the required resolution. This problem has been overcome by use of a combination of ion beam processing and ozone slimming to form lift-off patterns with undercuts from a single layer of photoresist. The ion beam process serves to harden the top portion of the resist while the ozone is used to oxidize and erode the lower portion resist sidewall to form the undercut.